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PRE
Amoldt
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8/21/00

In re Patent Application of :
Kevin K. Chan et al. : Group Art Unit: 2503
S.N. To be assigned :
Filed: Herewith : Examiner: S. Meier
For: A Scalable MOS Field Effect Transistor

PRELIMINARY AMENDMENT

Assistant Commissioner of Patents
Washington, D. C. 20231

Sir:

Please amend the prior application, Serial No. 08/683,329, as follows:

In the Specification

Page 2, line 11, change "width" to --gate length--; same line, after "scaled" insert --to smaller dimensions--.

Page 6, after line 13, insert

3 --Fig. 21 shows a schematic view of an electrochemical anodic oxidation set-up.

Fig. 22 shows a top view of several gate oxide regions during a step in fabricating a sixth embodiment of the invention.

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